

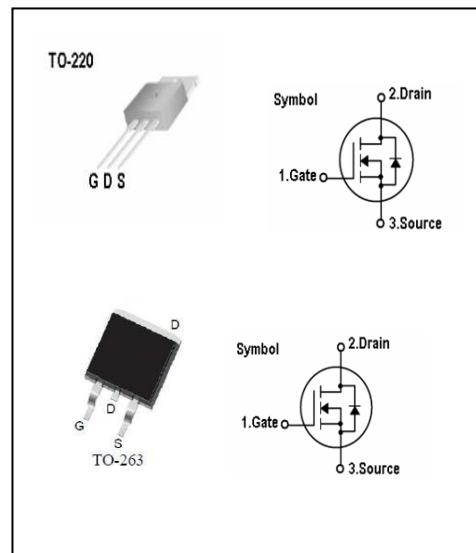
N-Channel MOSFET

Features

- 68V, 80A, Rds(on)(typ)=6.5mΩ @ Vgs=10V
- High Ruggedness
- Fast Switching
- 100% Avalanche Tested
- Improved dv/dt Capability

General Description

This Power MOSFET is produced using Si-Tech's advanced Trench MOS Technology. This latest technology has been especially designed to minimize on-state resistance, have a high rugged avalanche characteristics. These devices are well suited for low voltage application such as automotive, DC/DC converters, and high efficiency switch for power management in portable and battery products.



Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V _{DSS}	Drain-Source Voltage	68	V
I _D	Continuous Drain Current (TC=25 °C)	80	A
	Continuous Drain Current (TC=100°C)	65	A
I _{DM}	Pulsed Drain Current (Note 1)	260	A
V _{GS}	Gate-Source Voltage	±25	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	471	mJ
P _D	Maximum Power Dissipation (TC=25 °C)	176	W
	Derating Factor above 25°C	1.18	W/°C
T _J	Operating Junction Temperature Range	-55 to +175	°C
T _{STG}	Storage Temperature Range	-55 to +175	°C

Thermal Characteristics

Symbol	Parameter	Max.	Units
R _{th j-c}	Thermal Resistance, Junction to case	0.85	°C/W
R _{th c-s}	Thermal Resistance, Case to Sink	0.5	°C/W
R _{th j-a}	Thermal Resistance, Junction to Ambient	62.5	°C/W

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	68	-	-	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =65V, V _{GS} =0V	-	-	1	uA
I _{GSS}	Gate Leakage Current, Forward	V _{GS} =25V, V _{DS} =0V	-	-	100	nA
	Gate Leakage Current, Reverse	V _{GS} =-25V, V _{DS} =0V	-	-	-100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	2.5	-	3.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =40A	-	6.5	7.2	mΩ
Q _g	Total Gate Charge	V _{DD} =60V	-	80	-	nC
Q _{gs}	Gate-Source Charge	V _{GS} =10V	-	11	-	nC
Q _{gd}	Gate-Drain Charge	I _D =80A (Note 3)	-	20	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =37.5V, V _{GS} =10V	-	27	-	ns
t _r	Turn-on Rise Time	I _D =45A, R _G =4.7Ω	-	25	-	ns
t _{d(off)}	Turn-off Delay Time	T _C =25 °C	-	105	-	ns
t _f	Turn-off Fall Time	(Note 3)	-	58	-	ns
C _{iss}	Input Capacitance -	V _{DS} =25V	-	4040	-	pF
C _{oss}	Output Capacitance	V _{GS} =0V	-	388	-	pF
C _{rss}	Reverse Transfer Capacitance	f = 1MHz	-	294	-	pF

Source-Drain Diode Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

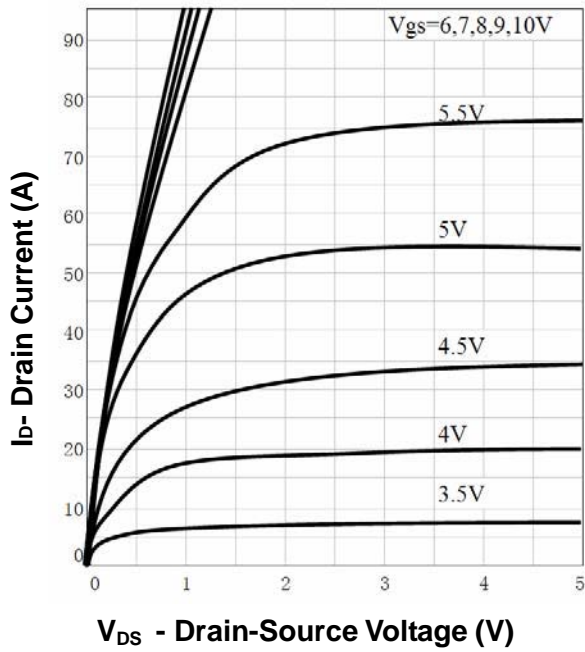
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I _s	Continuous Source Diode Forward Current		-	-	80	A
I _{SM}	Pulsed Source Diode Forward Current (Note 1)		-	-	260	A
V _{SD}	Forward On Voltage	V _{GS} =0V, I _s =45A	-	-	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} =0V, I _s =45A	-	50		ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt = 100A/us	-	90		nC

Notes:

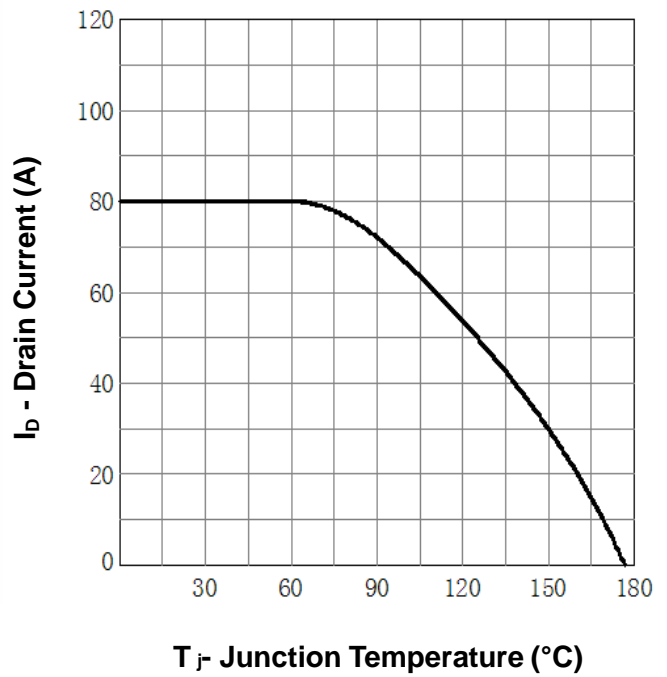
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L=0.5mH, V_{DD}=50V, R_G=25Ω, Starting T_J=25°C
3. Pulse Width ≤ 300 us; Duty Cycle ≤ 2%

Typical Characteristics

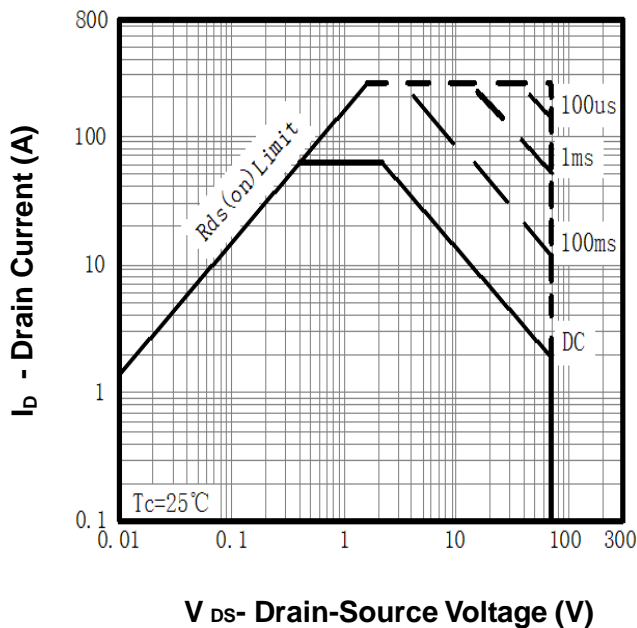
Output Characteristics



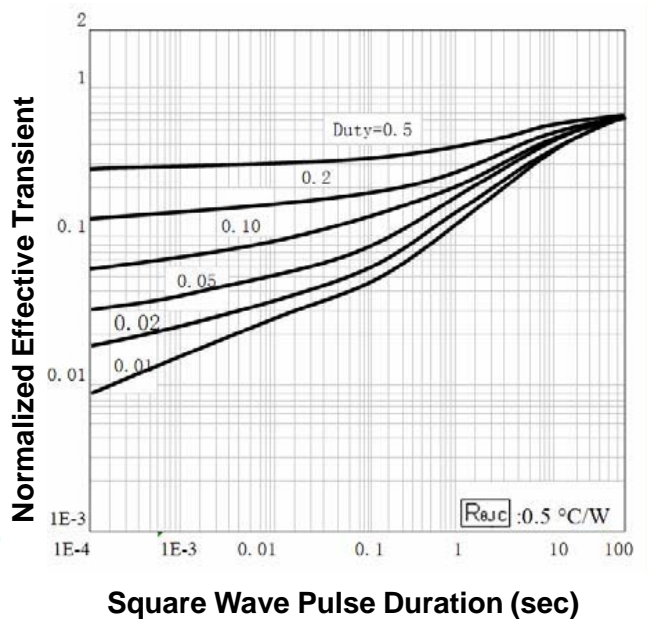
Drain Current



Safe Operation Area

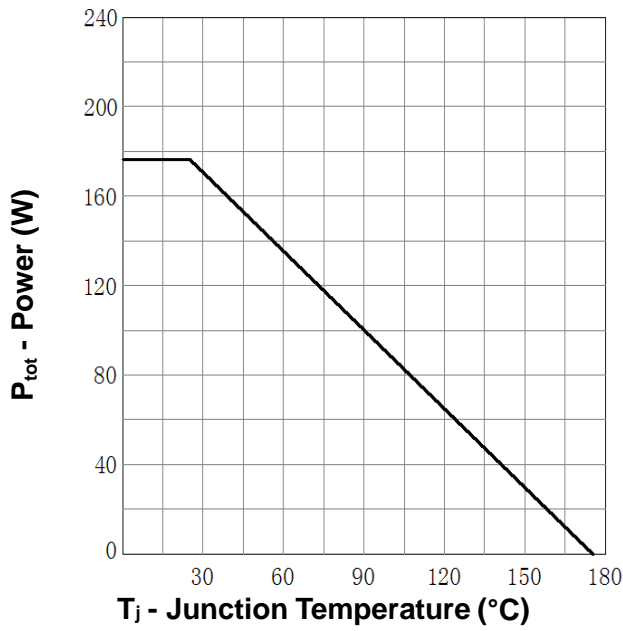


Thermal Transient Impedance

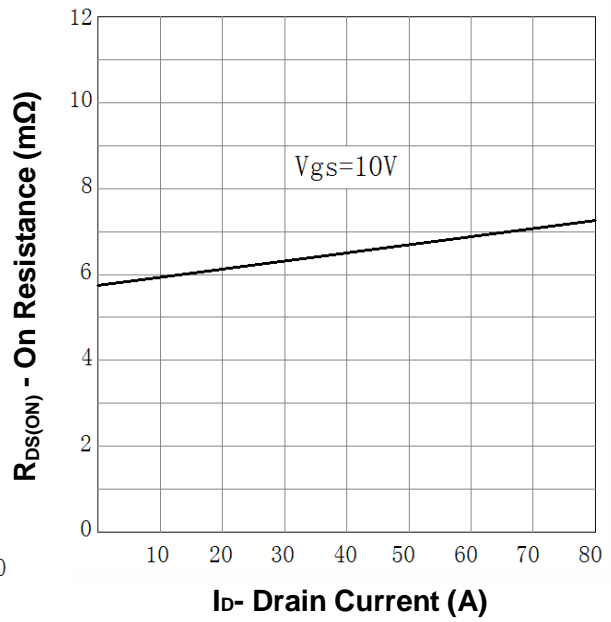


Typical Characteristics

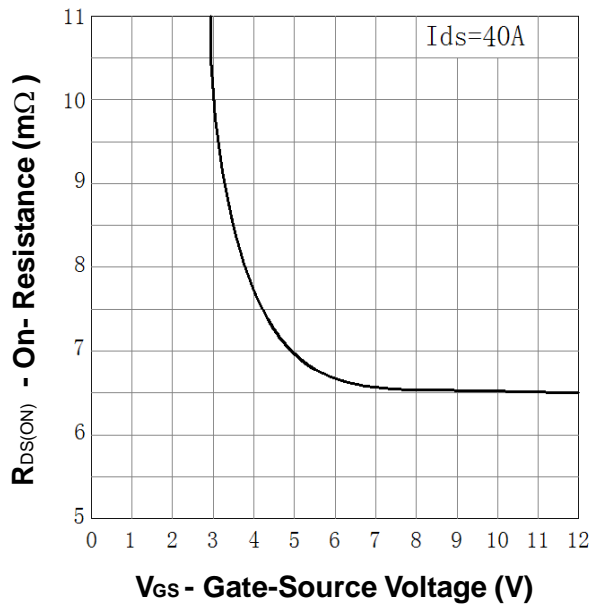
Power Dissipation



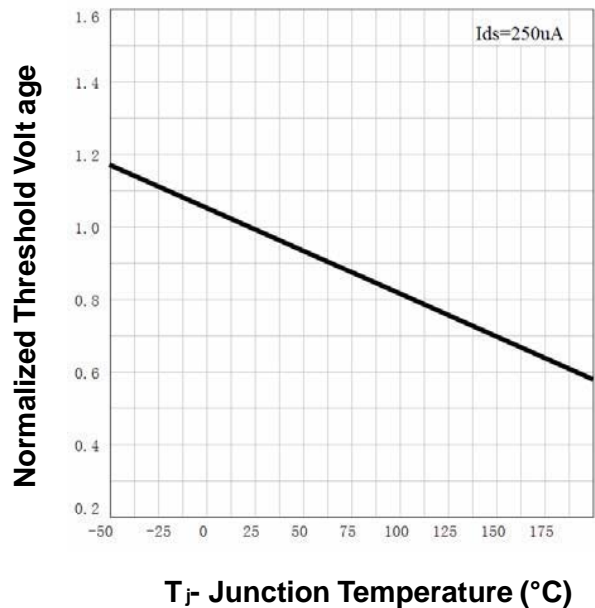
Drain-Source On Resistance



Drain-Source On Resistance

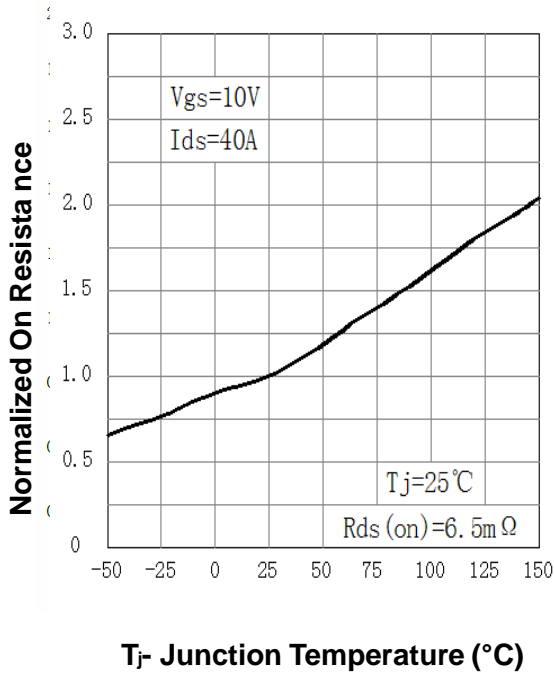


Gate Threshold Voltage

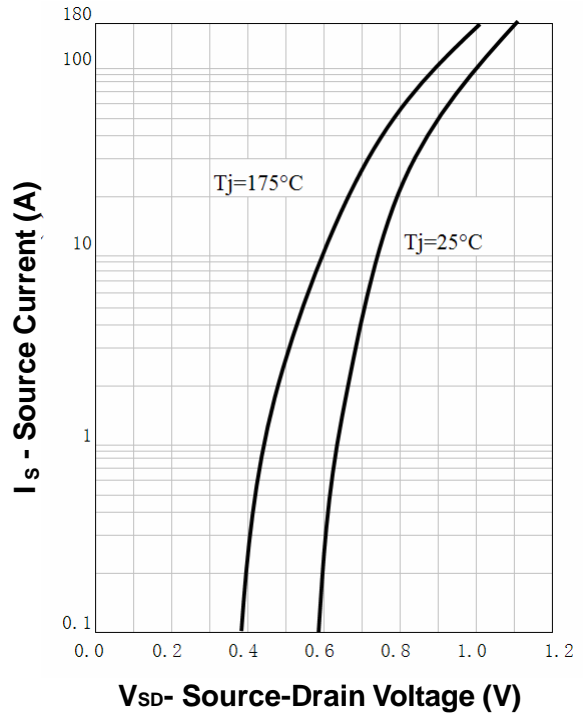


Typical Characteristics

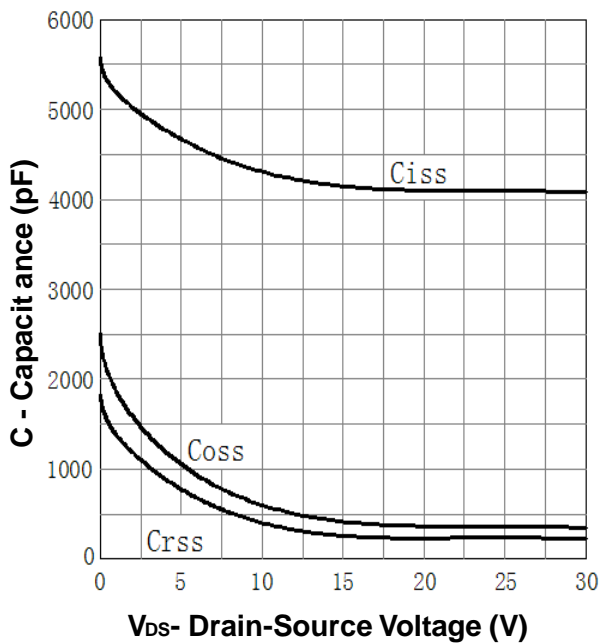
Drain-Source On Resistance



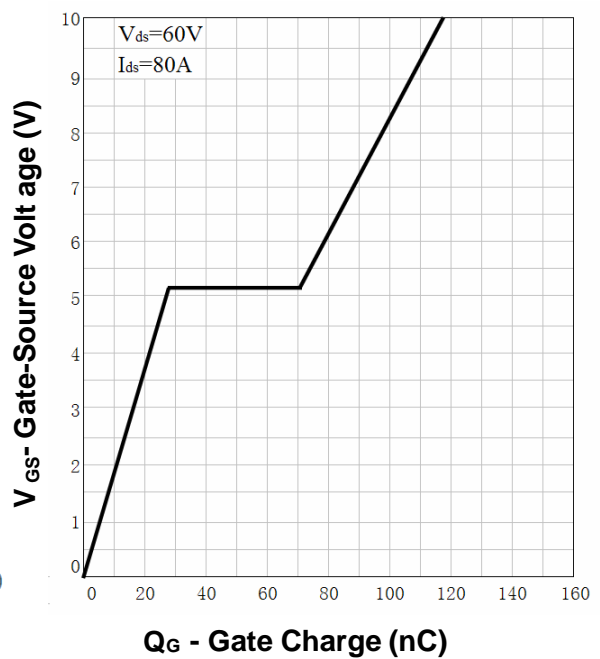
Source-Drain Diode Forward



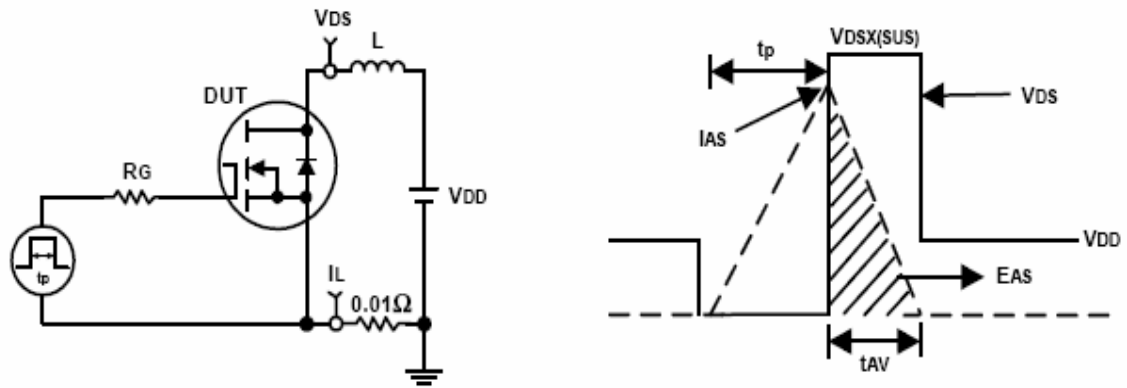
Capacitance



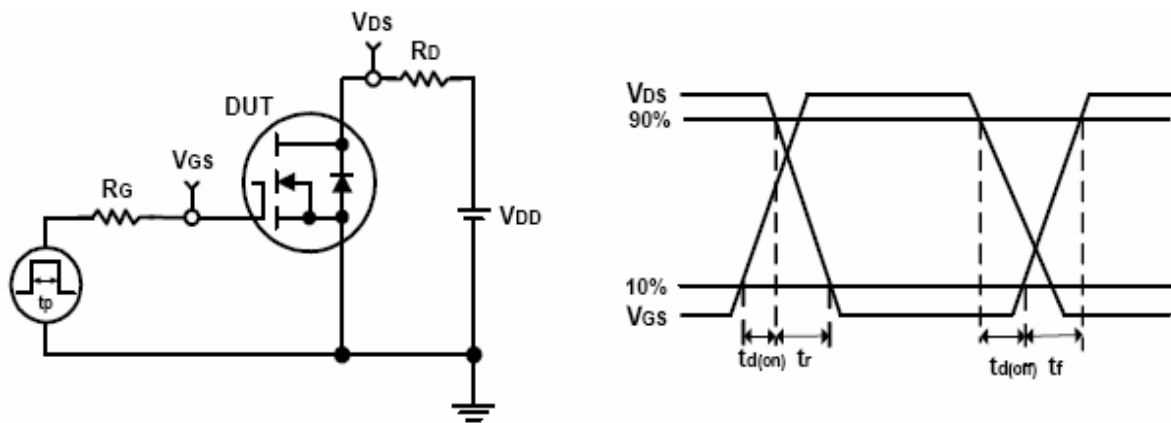
Gate Charge



Avalanche Test Circuit and Waveforms



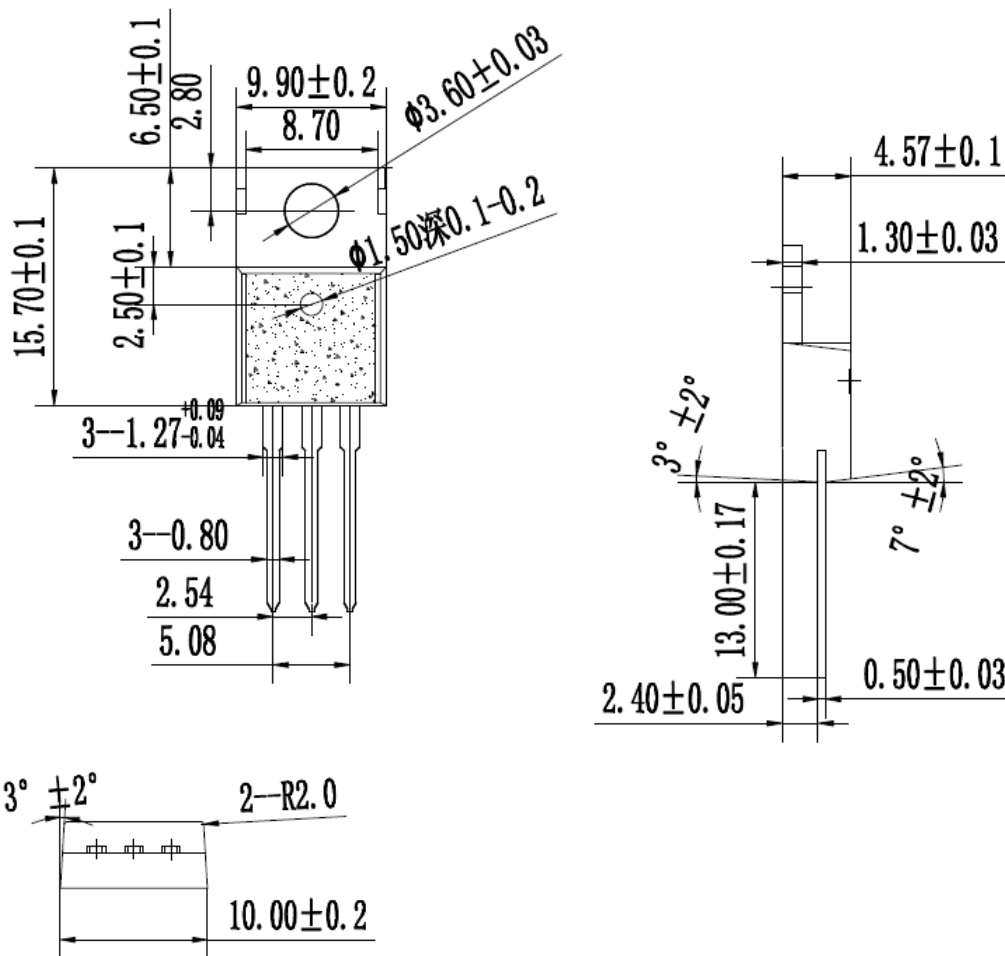
Switching Time Test Circuit and Waveforms



Package Outline

Dimensions are shown in millimeters

R: TO220



S: TO263 (D²PAK)

